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ABSTRACT

5 A method of manufacturing a crystalline silicon film excellent in crystallinity. When using elements such as nickel as metal elements that promotes the crystallization of the amorphous silicon film, nickel is allowed to be contained in a solution repelled by the surface of the amorphous silicon film. Then, a part of the amorphous silicon film is removed, and the solution is held in only that part. In this way, the nickel elements are selectively introduced into a part of the amorphous silicon film, and a heat treatment is also conducted to allow crystal growth to proceed from that portion toward a direction parallel to a substrate.

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